# **CPH6444**

# ON Semiconductor®

# N-Channel Power MOSFET 60V, 4.5A, 78mΩ, Single CPH6

http://onsemi.com

#### **Features**

- · Low ON-resistance
- 4V drive

- · Protection diode in
- · Halogen free compliance

#### **Specifications**

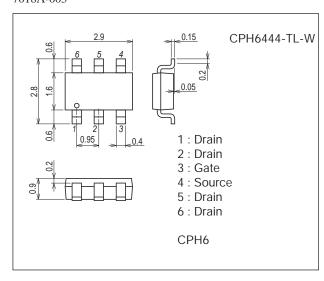
#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain to Source Voltage	V <sub>DSS</sub>		60	V
Gate to Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		4.5	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	18	Α
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm <sup>2</sup> x0.8mm)	1.6	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

#### **Package Dimensions**

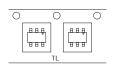
unit : mm (typ) 7018A-003



#### **Ordering & Package Information**

Device	Package	Shipping	memo	
CPH6444-TL-W	CPH6 SC-74, SOT-26, SOT-457	3,000 pcs./reel	Pb-Free and Halogen Free	

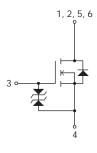
#### Packing Type: TL



#### Marking



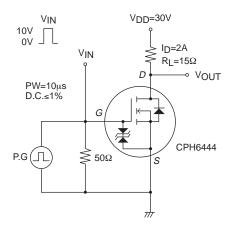
#### **Electrical Connection**

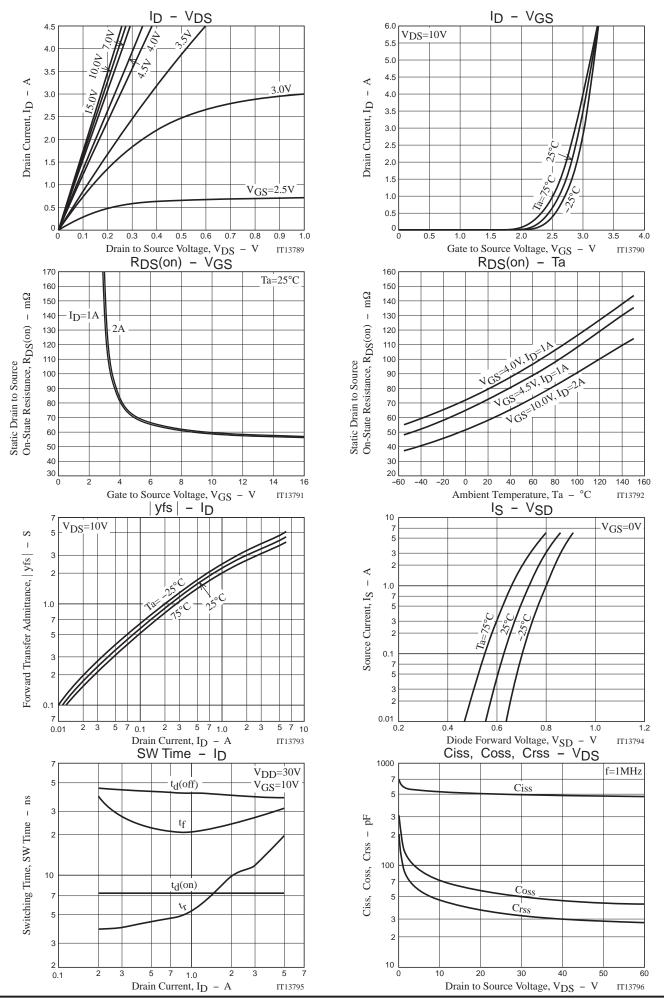


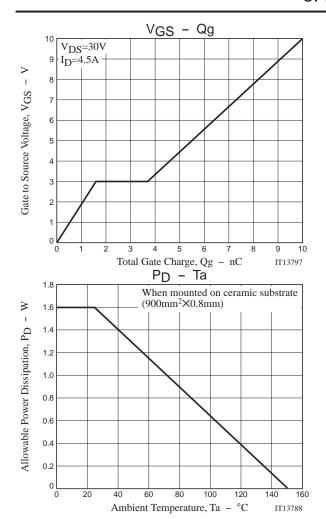
#### Electrical Characteristics at Ta=25°C

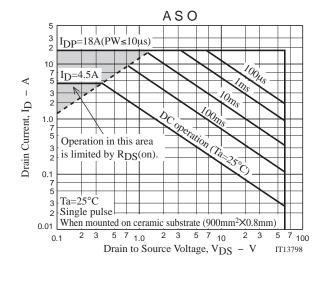
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	60			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V			1	μΑ
Gate to Source Leakage Current	IGSS	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μΑ
Cutoff Voltage	VGS(off)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.2		2.6	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> =10V, I <sub>D</sub> =2A	1.8	3		S
Static Drain to Source On-State Resistance	R <sub>DS</sub> (on)1	I <sub>D</sub> =2A, V <sub>GS</sub> =10V		60	78	mΩ
	R <sub>DS</sub> (on)2	I <sub>D</sub> =1A, V <sub>G</sub> S=4.5V		74	104	mΩ
	R <sub>DS</sub> (on)3	I <sub>D</sub> =1A, V <sub>G</sub> S=4V		81	114	mΩ
Input Capacitance	Ciss	V <sub>DS</sub> =20V, f=1MHz		505		pF
Output Capacitance	Coss			57		pF
Reverse Transfer Capacitance	Crss			37		pF
Turn-ON Delay Time	t <sub>d</sub> (on)	See specified Test Circuit.		7.3		ns
Rise Time	t <sub>r</sub>			9.8		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)			40		ns
Fall Time	tf			24		ns
Total Gate Charge	Qg	V <sub>DS</sub> =30V, V <sub>GS</sub> =10V, I <sub>D</sub> =4.5A		10		nC
Gate to Source Charge	Qgs			1.6		nC
Gate to Drain "Miller" Charge	Qgd			2.1		nC
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =4.5A, V <sub>GS</sub> =0V		0.83	1.2	V

#### Switching Time Test Circuit



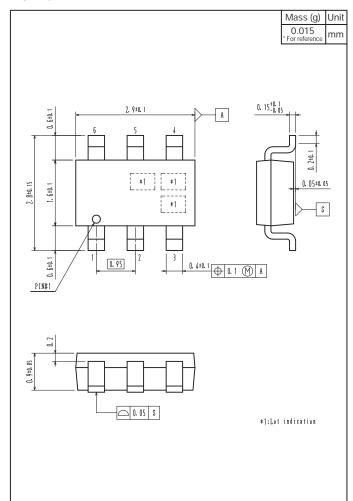




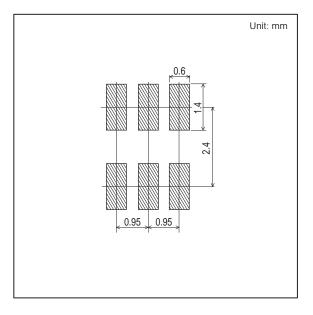


### **Outline Drawing**

## CPH6444-TL-W



#### Land Pattern Example



Note on usage: Since the CPH6444 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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